

40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) Max	I _D Tc = +25°C (Note 7)
40V	3.3mΩ @ V _{GS} = 10V	100A
40 V	5.0mΩ @ V _{GS} = 5V	95A

Description

This new generation n-channel enhancement mode MOSFET is designed to minimize RDS(ON) yet maintain superior switching performance.

Applications

- **BLDC** motors
- **DC-DC** converters
- Load switches

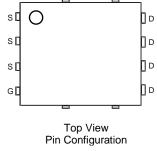
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable And Robust End Application
- Low RDS(ON) Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/guality/product-definitions/
- An automotive-compliant part is available under separate datasheet (DMTH43M8LPSQ)

Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

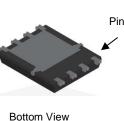


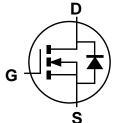


Site1:

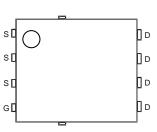


Top View





Internal Schematic



Top View

Pin Configuration

Ordering Information (Note 4)

Part Number	Paakaga	Packing		
Part Number	Package	Qty.	Carrier	
DMTH43M8LPS-13	PowerDI5060-8	2,500	Tape & Reel	
DMTH43M8LPS-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. Notes:

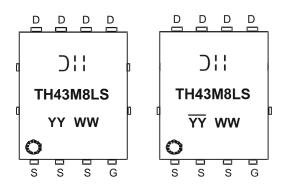
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and l ead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



 $\begin{array}{l} \bigcirc I & I = Manufacturer's Marking \\ TH43M8LS or TH4008LS = Product Type Marking Code \\ \underline{YYWW} = Date Code Marking \\ \underline{YY or YY} = Last Two Digits of Year (ex: 23 = 2023) \\ WW = Week Code (01 to 53) \end{array}$

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current, V _{GS} = 10V (Note 5)	T _A = +25°C T _A = +100°C	D	22 15.5	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) (Note 7)	T _C = +25°C T _C = +100°C	۱ _D	100 82	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	350	А
Maximum Continuous Body Diode Forward Current (Note 6)		ls	69	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		lsм	350	А
Avalanche Current, L = 1mH		las	13.2	А
Avalanche Energy, L = 1mH		E _{AS}	87	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	55	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	PD	83	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	1.8	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

 Notes:
 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

 6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Package limit.

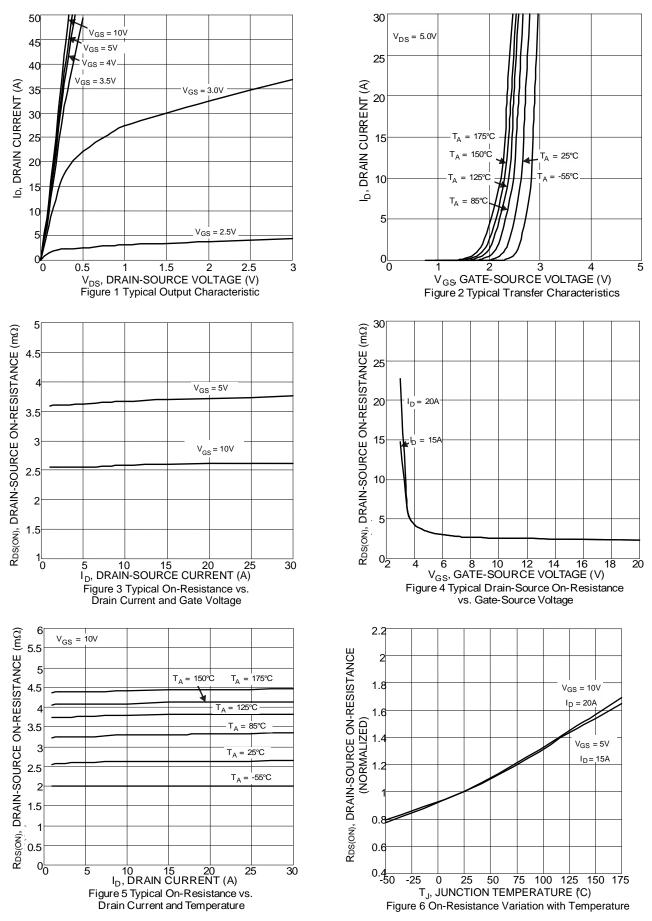


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BVDSS	40	—		V	$V_{GS} = 0V, I_D = 1mA$
Zero Gate Voltage Drain Current	IDSS		—	1	μA	$V_{DS} = 32V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	VGS(TH)	1	—	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Bacon		2.7	3.3	mΩ	$V_{GS} = 10V, I_{D} = 20A$
Static Drain-Source On-Resistance	Rds(on)		3.6	5.0	11152	$V_{GS} = 5V, I_{D} = 15A$
Diode Forward Voltage	V _{SD}	_	—	1.2	V	$V_{GS} = 0V, I_{S} = 20A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss		2,693	—		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz
Output Capacitance	Coss		1,172	—	pF	
Reverse Transfer Capacitance	Crss		52	_		
Gate Resistance	Rg		2.54	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (VGS = 10V)	QG		38.5	_		
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}		17.6	_	nC	V _{DS} = 30V, I _D = 20A
Gate-Source Charge	Q _{GS}	_	6.9		IIC IIC	
Gate-Drain Charge	Q _{GD}	—	6.9	_		
Turn-On Delay Time	t _{D(ON)}	—	5.2	_		
Turn-On Rise Time	tR	_	5.7	—	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 20A, R_G = 3\Omega$
Turn-Off Delay Time	tD(OFF)	_	23.5			
Turn-Off Fall Time	tF		11	—	1	
Body Diode Reverse Recovery Time	trr		35.4	—	ns	
Body Diode Reverse Recovery Charge	Q _{RR}		32.9	_	nC	$I_F = 20A, di/dt = 100A/\mu s$

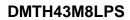
Notes:8. Short duration pulse test used to minimize self-heating effect.9. Guaranteed by design. Not subject to product testing.

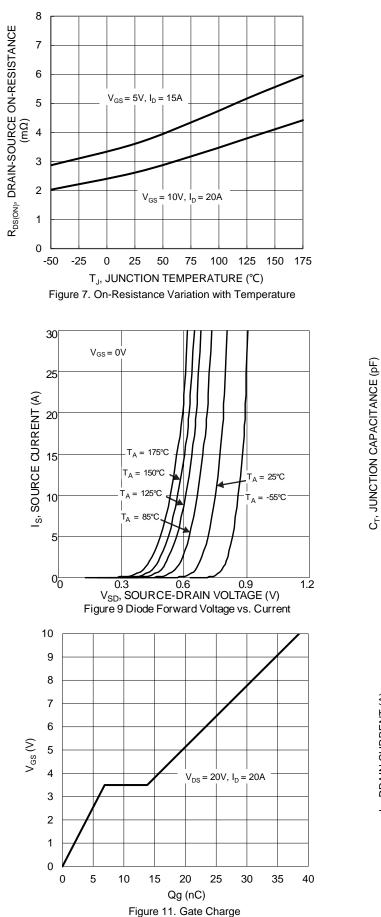




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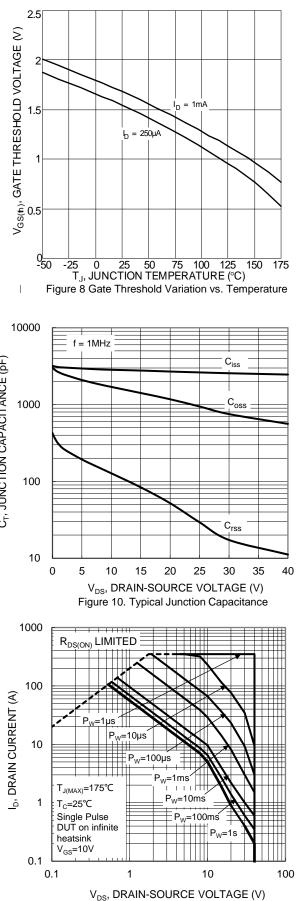
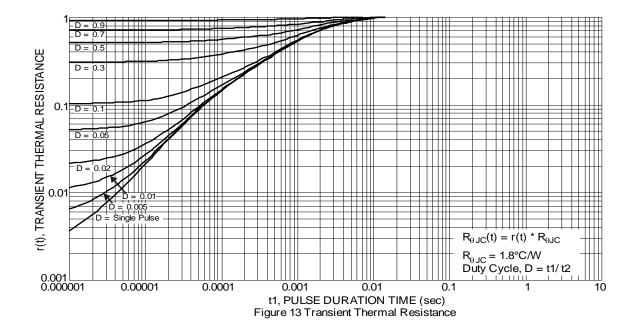


Figure 12. SOA, Safe Operation Area

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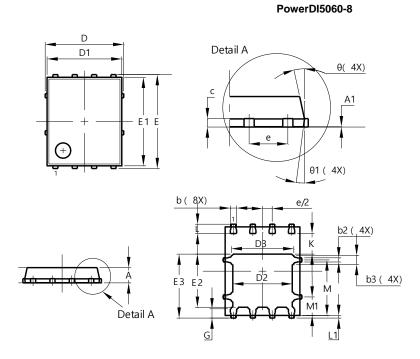




Package Outline Dimensions

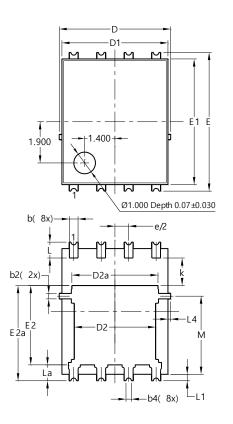
Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

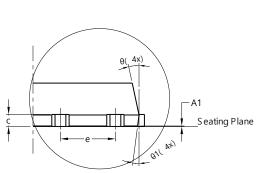


	PowerDI5060-8					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
C	0.230	0.330	0.277			
D	ļ	5.15 BSC				
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
Е	(6.15 BSC				
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е		1.27 BSC	;			
G	0.51	0.71	0.61			
К	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
Al	All Dimensions in mm					

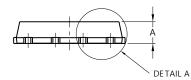
Site 2:



PowerDI5060-8/SWP (Type UX)



DETAIL A



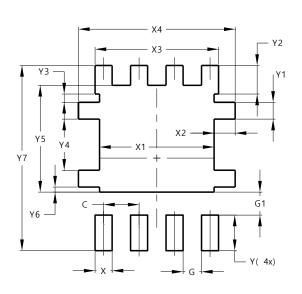
PowerDI5060-8/SWP (Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4).25REF		
C	0.230	0.330	0.277	
D	5	.15 BS0	2	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
ш	6	.40 BS0	2	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е	1	.27BSC)	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0	.050RE		
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All	All Dimensions in mm			



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

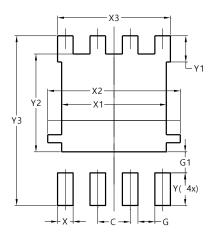


Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)

PowerDI5060-8



Dimensions	Value (in mm)	
С	1.270	
G	0.660	
G1	0.820	
Х	0.610	
X1	4.100	
X2	5.190	
X3	4.420	
Y	1.270	
Y1	1.020	
Y2	3.810	
Y3	6.610	



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